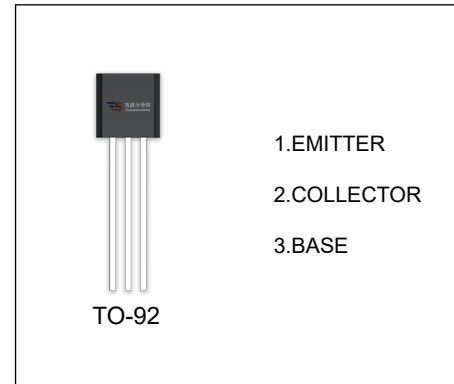


**B772S** TRANSISTOR (PNP)

**FEATURES**

- Low speed switching


**ORDERING INFORMATION**

Part Number	Package	Packing Method	Pack Quantity
B772S	TO-92	Bulk	1000pcs/Bag
B772S-TA	TO-92	Tape	2000pcs/Box

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-30	V
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V
I <sub>C</sub>	Collector Current -Continuous	-3	A
P <sub>C</sub>	Collector Power Dissipation	0.625	W
R <sub>θJA</sub>	Thermal Resistance, junction to Ambient	200	°C /W
T <sub>J</sub> , T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~150	°C

$T_a=25\text{ }^\circ\text{C}$  unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_C=0$	-6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-40\text{V}, I_E=0$			-1	$\mu\text{A}$
Collector cut-off current	$I_{CEO}$	$V_{CE}=-30\text{V}, I_B=0$			-10	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-6\text{V}, I_C=0$			-1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=-2\text{V}, I_C=-1\text{A}$	60		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2\text{A}, I_B=-0.2\text{A}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-2\text{A}, I_B=-0.2\text{A}$			-1.5	V
Transition frequency	$f_T$	$V_{CE}=-5\text{V}, I_C=-0.1\text{A}$ $f=10\text{MHz}$	50	80		MHz

#### CLASSIFICATION OF $h_{FE}$

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

